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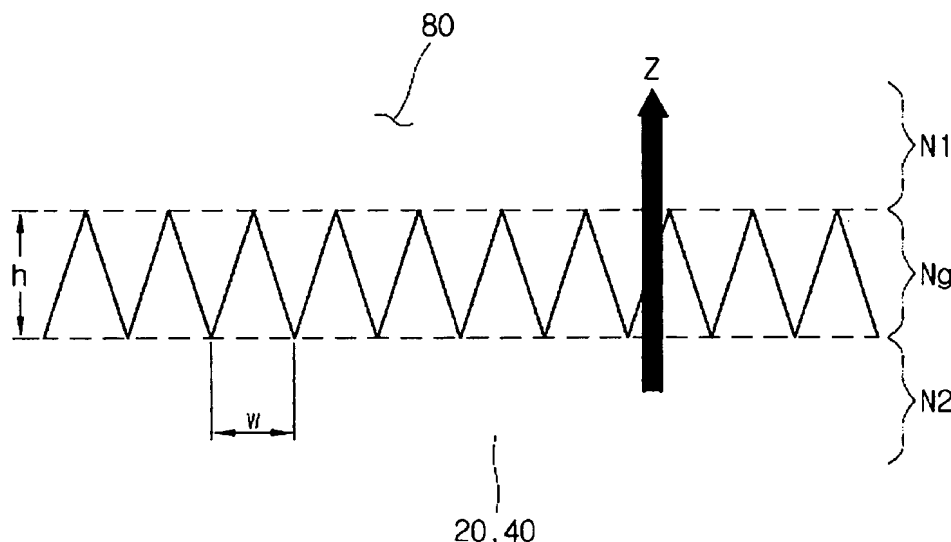
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(54) Title: **ANTI-REFLECTED HIGH EFFICIENCY LIGHT EMITTING DIODE DEVICE**



(57) Abstract: The present invention is related to a light emitting diode device in which a fine prominence and depression is formed on a semiconductor layer to make an anti-reflection region. The light emitting diode device comprises, a substrate; a N-type semiconductor layer; an active layer for generating light; P-type semiconductor layer; a first exposed region formed by etching the active layer and the P-type semiconductor layer to partly expose the N-type semiconductor layer; a first ohmic contact formed on the first exposed layer; a second ohmic contact formed on the P-type semiconductor layer, and having an opening to partly form a second exposed region on the P-type semiconductor layer, said second exposed layer being formed to partly have a ultra-fine prominence and depression.



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